

### 2N6770T1 Information

Heisener.com

2N6770T1 Part Number

Manufacturer Microsemi Corporation

Discrete Semiconductor Products Category

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 12A TO-254AA TO-254-3, TO-254AA (Straight Leads) **Package** 

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only

E-mail: salesdept@heisener.com



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### **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# 2N6770T1 Specifications

Manufacturer Part Number         2N6770T1           Manufacturer         Microsemi Corporation           Category         Discrete Semiconductor Products		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-254-3, TO-254AA (Straight Leads)           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         12A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         120nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         -           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         4W (Ta), 150W (Tc)           Rds On (Max) @ Id, Vgs         500 mOhnm @ 12A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-254AA (Straight Leads)	Manufacturer Part Number	2N6770T1
Package         TO-254-3, TO-254AA (Straight Leads)           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         12A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         120nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         -           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         4W (Ta), 150W (Tc)           Rds On (Max) @ Id, Vgs         500 mOhm @ 12A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-254AA           Package / Case         TO-254AA (Straight Leads)	Manufacturer	Microsemi Corporation
PackageTO-254-3, TO-254AA (Straight Leads)Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C12A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs120nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)4W (Ta), 150W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-254AAPackage / CaseTO-254AA (Straight Leads)	Category	Discrete Semiconductor Products
Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C12A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs120nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)4W (Ta), 150W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-254AAPackage / CaseTO-254-3, TO-254AA (Straight Leads)		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  12A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  120nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  - Vgs (Max)  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  500 mOhm @ 12A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Supplier Device Package  TO-254AA  Package / Case  TO-254AA (Straight Leads)	Package	TO-254-3, TO-254AA (Straight Leads)
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 12A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 120nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 500 mOhm @ 12A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-254AA Package / Case  MOSFET (Metal Oxide)  500V  MOSFET (Metal Oxide)  500V  12A (Ta)  4V (@ 250µA  4V (@ 250µA  4V (@ 250µA  4V (@ 10V  4V (@ 10V  50V  50V  Through Hole Through Hole	Series	-
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C12A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs120nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)4W (Ta), 150W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-254AAPackage / CaseTO-254-3, TO-254AA (Straight Leads)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  - Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  12A (Ta)  14V  4V @ 250μA  12OnC @ 10V  - 4V (Ta) 150V  10V  - 50V  50V  Through Hole  12A, 10V  150°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs120nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)4W (Ta), 150W (Tc)Rds On (Max) @ Id, Vgs500 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-254AAPackage / CaseTO-254-3, TO-254AA (Straight Leads)	Drain to Source Voltage (Vdss)	500V
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Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds	Drive Voltage (Max Rds On, Min Rds On)	10V
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  500 mOhm @ 12A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-254AA  Package / Case  TO-254-3, TO-254AA (Straight Leads)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs500 mOhm @ 12A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-254AAPackage / CaseTO-254-3, TO-254AA (Straight Leads)	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-254AA  Package / Case  TO-254-3, TO-254AA (Straight Leads)	Power Dissipation (Max)	4W (Ta), 150W (Tc)
Mounting Type Through Hole Supplier Device Package TO-254AA Package / Case TO-254-3, TO-254AA (Straight Leads)	Rds On (Max) @ Id, Vgs	500 mOhm @ 12A, 10V
Supplier Device Package TO-254AA Package / Case TO-254-3, TO-254AA (Straight Leads)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-254-3, TO-254AA (Straight Leads)	Mounting Type	Through Hole
	Supplier Device Package	TO-254AA
Report errors?	Package / Case	TO-254-3, TO-254AA (Straight Leads)
*		Report errors?

### 2N6770T1 Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## 2N6770T1 Payment Methods





















## 2N6770T1 Shipping Methods













If you have any question about 2N6770T1, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com